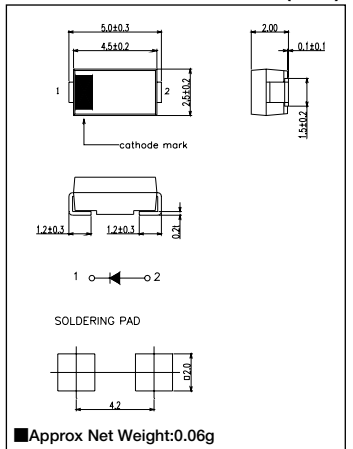


1A Avg. 100 Volts Standard Recovery Diode EC10DS1

■最大定格 Maximum Ratings

Item	Symbol	Conditions	Unit
くり返しピーク逆電圧 Repetitive Peak Reverse Voltage	V_{RRM}	100	V
非くり返しピーク逆電圧 Non-repetitive Peak Reverse Voltage	V_{RSM}	250	V
平均整流電流 Average Rectified Forward Current	I_O	50Hz, 正弦半波通電抵抗負荷 50Hz Half Sine Wave Resistive Load ($T_a=25^\circ\text{C}$)	0.74* ¹
			1.0* ²
実効順電流 R.M.S. Forward Current	$I_F(\text{RMS})$	1.57	A
サージ順電流 Surge Forward Current	I_{FSM}	25 50Hz正弦半波, 1サイクル, 非くり返し 50Hz Half Sine Wave, 1cycle, Non-repetitive	A
動作接合温度範囲 Operating Junction Temperature Range	T_{jw}	-40~+150	°C
保存温度範囲 Storage Temperature Range	T_{stg}	-40~+150	°C

■OUTLINE DRAWING(mm)



■電氣的・熱的特性 Electrical/Thermal Characteristics

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit	
ピーク逆電流 Peak Reverse Current	I_{RM}	$T_j=25^\circ\text{C}, V_{RM}=V_{RRM}$	—	—	10	μA	
ピーク順電圧 Peak Forward Voltage	V_{FM}	$T_j=25^\circ\text{C}, I_{FM}=1\text{A}$	—	—	1.1	V	
熱抵抗 Thermal Resistance	$R_{th(j-a)}$	接合部・周囲間 Junction to Ambient	*1	—	—	157	°C/W
			*2	—	—	108	°C/W

*1: プリント基板実装 / Glass Epoxy Substrate mounted (Soldering Land=2×2mm, Both Sides)
 *2: アルミナ基板実装 / Alumina Substrate mounted (Soldering Lands= 2×2 mm, Both Sides)

■定格・特性曲線

FIG.1

順電圧特性
FORWARD CURRENT VS. VOLTAGE

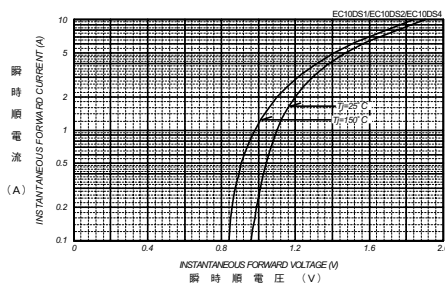


FIG.2

平均順電力損失特性
AVERAGE FORWARD POWER DISSIPATION

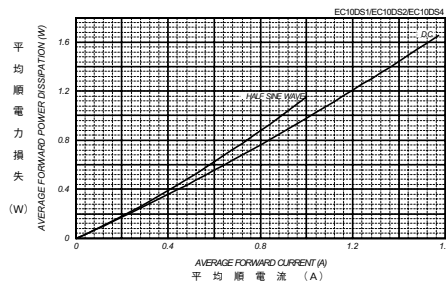


FIG.3

平均順電流一周囲温度定格
AVERAGE FORWARD CURRENT VS. AMBIENT TEMPERATURE

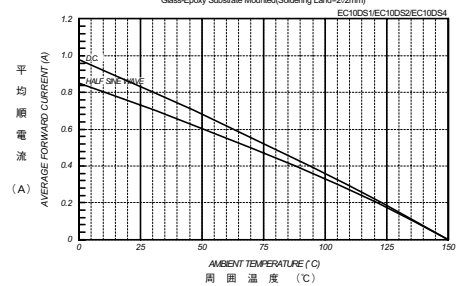


FIG.4

平均順電流一周囲温度定格
AVERAGE FORWARD CURRENT VS. AMBIENT TEMPERATURE

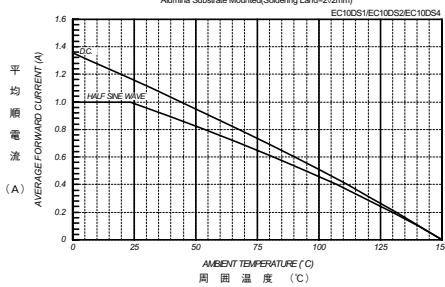


FIG.5

サージ順電流定格
SURGE CURRENT RATINGS

